1.0±0.1

Unit: mm

0.15+0.1

Emitter 3. Collector EIA): SC-75 SSMini3-G1 Package

2SB1463

Silicon PNP epitaxial planar type

For high breakdown voltage low-frequency amplification Complementary to 2SD2240

Features

- High collector-emitter voltage (Base open) V_{CEO}
- Low noise voltage NV
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

Absolute Maximum Ratings $T_a = 25^{\circ}C$

	• -a =						2
Parameter	Symbol	Rating	Unit			0 ZE-10 1	2
Collector-base voltage (Emitter open)	V _{CBO}	-150	V			0 to 0.1 0.45±0.1	2
Collector-emitter voltage (Base open)	V _{CEO}	-150	V			9 0 14 4 0 0	\sim^{2}
Emitter-base voltage (Collector open)	V _{EBO}	-5	V			~ cos	SMir
Collector current	Ic	-50	mA				<u> </u>
Peak collector current	I _{CP}	-100	mA	Marking	Symbol	יי גע	7
Collector power dissipation	P _C	125	mW		X	in on	
Junction temperature	Tj	125	°C		6 10		
Storage temperature	T _{stg}	-55 to +125	°C		.00		
Electrical Characteristics	$\Gamma_{\rm a} = 25^{\circ} C$	C±3°C	JR	Marking S			
Parameter	Symbo		Conditions) .,	Min	Тур	M
Collector-emitter voltage (Base open)	VCEO	$I_{\rm C} = -100$	$\mu A, I_B = 0$		-150		
Emitter-base voltage (Collector open)	V _{EBO}	I _E = 10 μ	$A, I_0 = 0$		-5		

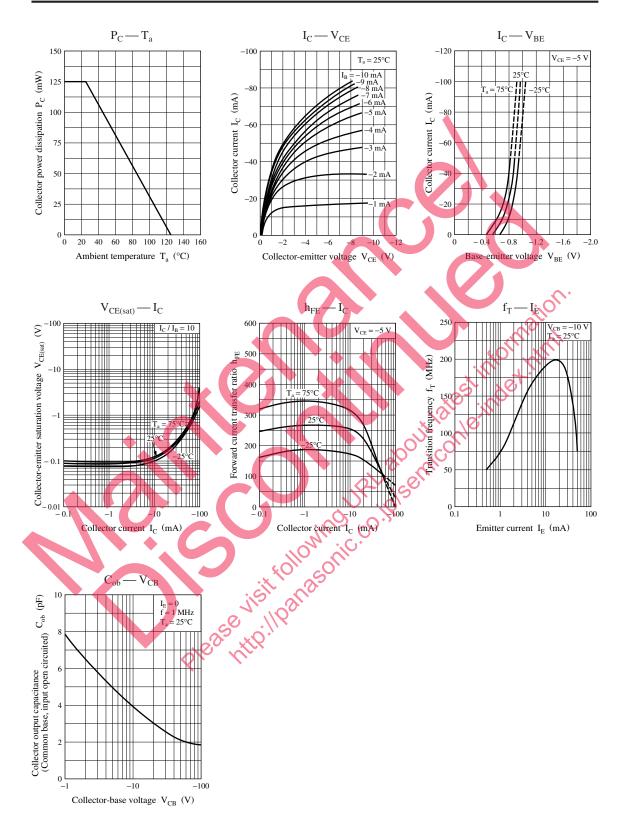


Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	VCEO	$I_{\rm C} = -100 \mu A, I_{\rm B} = 0$	-150			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm H} = -10 \ \mu A, I_{\rm O} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = -100 \text{ V}, I_E = 0$			-1	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = 5 V, I_C = -10 mA$	130		450	_
Collector-emitter saturation voltage	VeE(sat)	$I_{\rm C} = -30 \text{ mA}, I_{\rm B} = -3 \text{ mA}$			-1	V
Transition frequency	f _T	$\dot{V}_{CB} = -10 \text{ V}, \text{ I}_{\text{E}} = 10 \text{ mA}, \text{ f} = 200 \text{ MHz}$		200		MHz
Collector output capacitance	Cob	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4		pF
(Common base, input open circuited)						
Noise voltage	NV	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}, G_V = 80 \text{ dB}$		150		mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S	Т
h _{FE}	130 to 220	185 to 330	260 to 450



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